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MGFC36V7785A

7.7 ~ 8.5GHz BAND 4W INTERNALLY MATCHED GaAs FET

DESCRIPTION

The MGFC36V7785A is an internally impedance-matched GaAs power FET especially designed for use in 7.7 ~ 8.5 GHz band amplifiers.The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Class A operation
Internally matched to 50(ohm) system
High output power
P1dB = 4W (TYP.) @ f=7.7~8.5GHz
High power gain
GLP = 8 dB (TYP.) @ f=7.7~8.5GHz
High power added efficiency
P.A.E. = 29 % (TYP.) @ f=7.7~8.5GHz
Low distortion [item -51]
IM3= -45 dBc(TYP.) @Po=25dBm S.C.L.

APPLICATION

item 01 : 7.7~8.5 GHz band power amplifier
item 51 : 7.7~8.5 GHz band digital radio communication

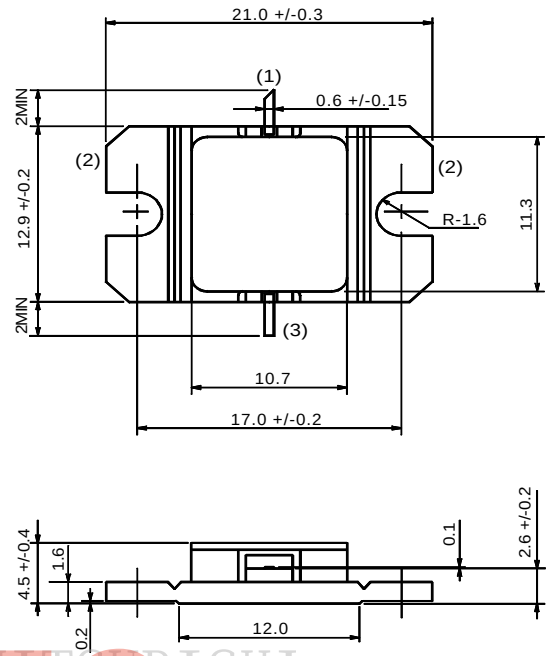
QUALITY GRADE

IG

RECOMMENDED BIAS CONDITIONS

VDS = 10 (V)
ID = 1.2 (A) Refer to Bias Procedure
RG= 100 (ohm)

OUTLINE DRAWING Unit : millimeters



GF-8

(1) GATE
(2) SOURCE (FLANGE)
(3) DRAIN

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ABSOLUTE MAXIMUM RATINGS (Ta=25 deg.C)

Symbol	Parameter	Ratings	Unit
VGDO	Gate to drain voltage	-15	V
VGSO	Gate to source voltage	-15	V
ID	Drain current	3.75	A
IGR	Reverse gate current	-10	mA
IGF	Forward gate current	21	mA
PT	Total power dissipation *1	25	W
Tch	Channel temperature	175	deg.C
Tstg	Storage temperature	-65 / +175	deg.C

*1 : Tc=25 deg.C

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ELECTRICAL CHARACTERISTICS (Ta=25 deg.C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
IDSS	Saturated drain current	VDS=3V, VGS=0V	-	-	3.75	A
gm	Transconductance	VDS=3V, ID=1.1A	-	1	-	S
VGS(off)	Gate to source cut-off voltage	VDS=3V, ID=10mA	-	-	-4.5	V
P1dB	Output power at 1dB gain compression	VDS=10V, ID(RF off)=1.2A, f=7.7~8.5GHz	35	36.5	-	dBm
GLP	Linear power gain		7	8	-	dB
ID	Drain current		-	-	1.8	A
P.A.E.	Power added efficiency		-	29	-	%
IM3	3rd order IM distortion *1		-42	-45	-	dBc
Rth(ch-c)	Thermal resistance *2	Delta Vf method	-	5	6	deg.C/W

*1 : item -51, 2 tone test, Po=25dBm Single Carrier Level, f=8.5GHz, Delta f=10MHz
*2 : Channel to case

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